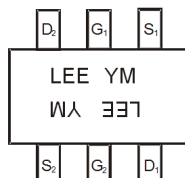


Marking Information



LEE = Product Type Marking Code
 YM = Date Code Marking
 Y or Y = Year (ex: I = 2021)
 M or M = Month (ex: 9 = September)

Date Code Key

Year	2016	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	D	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Unit
Drain-Source Voltage				V _{DSS}	60	V
Gate-Source Voltage				V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	350 290	mA	
Maximum Continuous Body Diode Forward Current (Note 6)				I _S	350	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	400	°C/W
Total Power Dissipation (Note 6)		P _D	410	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	312	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.2	2.0	Ω	$V_{GS} = 4.5V, I_D = 0.1A$
			1.4	2.5		$V_{GS} = 2.5V, I_D = 0.05A$
			1.8	3.0		$V_{GS} = 1.8V, I_D = 0.05A$
Forward Transconductance	$ Y_{fs} $	—	1.8	—	S	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}	—	0.8	1.3	V	$V_{GS} = 0V, I_S = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	32	—	pF	$V_{DS} = 30V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	3.9	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.4	—	pF	
Gate Resistance	R_g	—	101	—	Ω	$f = 1MHz, V_{GS} = 0V, V_{DS} = 0V$
Total Gate Charge	Q_g	—	0.5	—	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 250mA$
Gate-Source Charge	Q_{gs}	—	0.09	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.09	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	2.4	—	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 25\Omega, I_D = 200mA$
Turn-On Rise Time	t_R	—	2.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	22.6	—	ns	
Turn-Off Fall Time	t_F	—	12.5	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

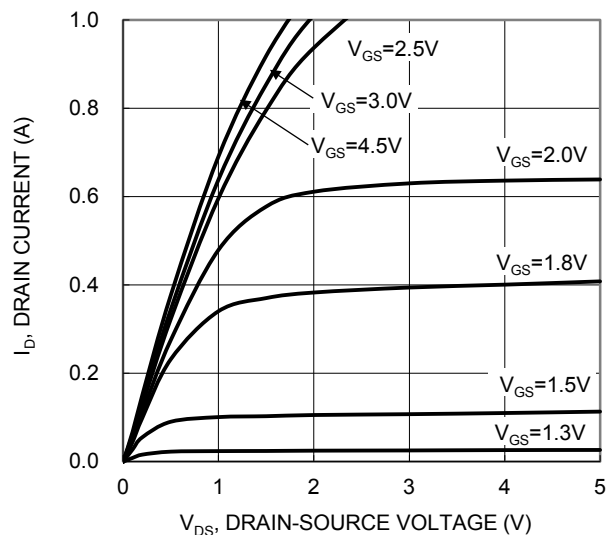


Figure 1. Typical Output Characteristic

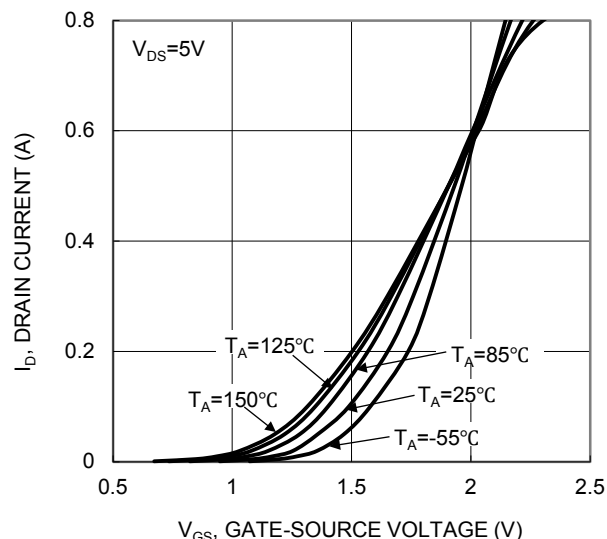


Figure 2. Typical Transfer Characteristic

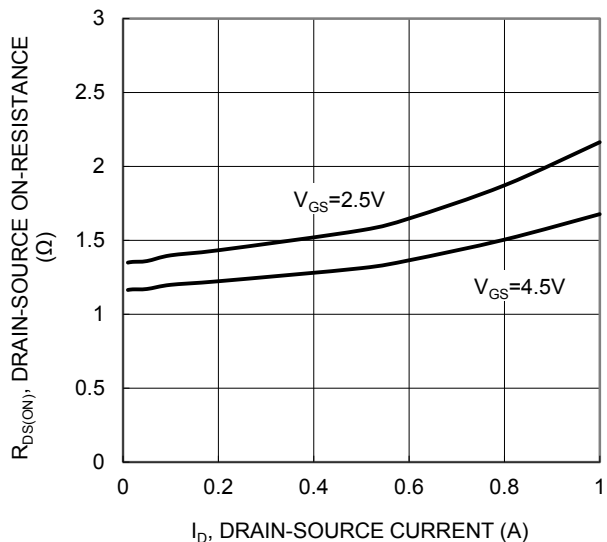


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

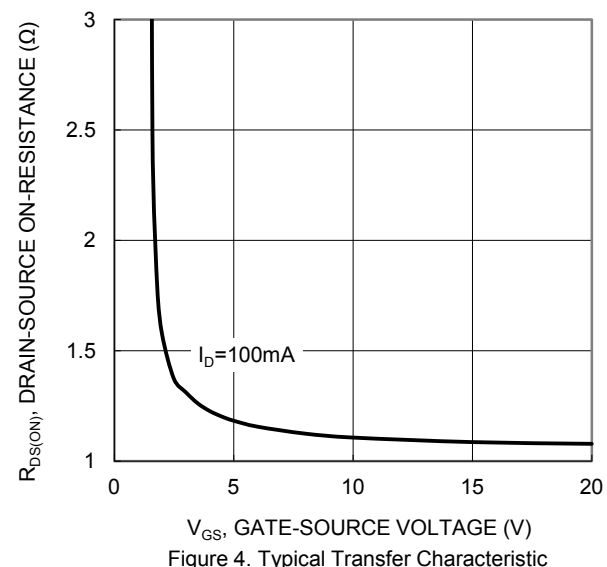


Figure 4. Typical Transfer Characteristic

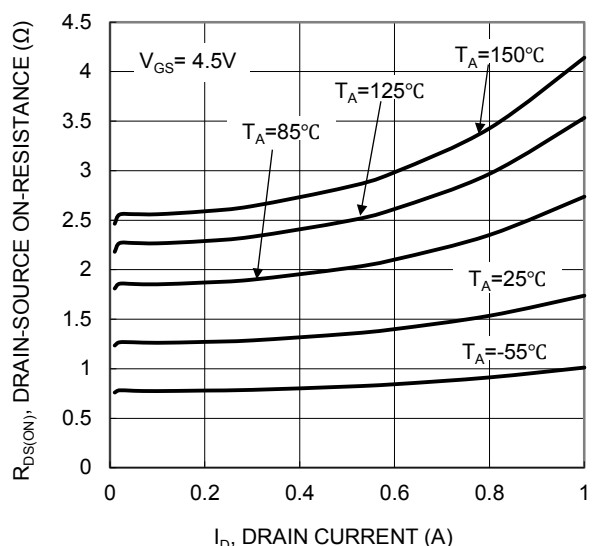


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

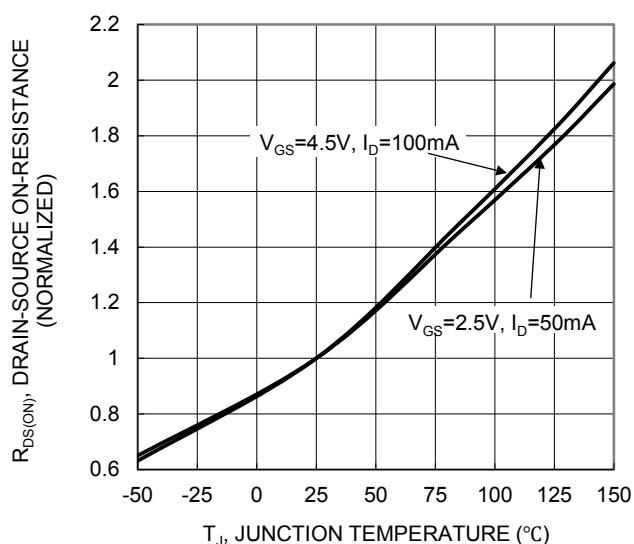


Figure 6. On-Resistance Variation with Junction Temperature

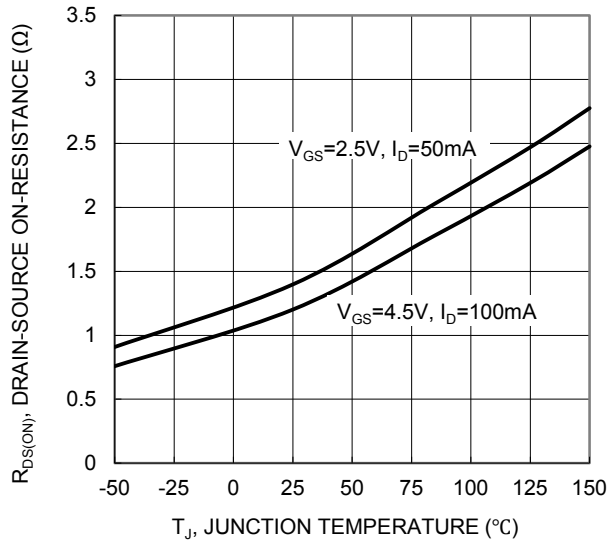


Figure 7. On-Resistance Variation with Junction Temperature

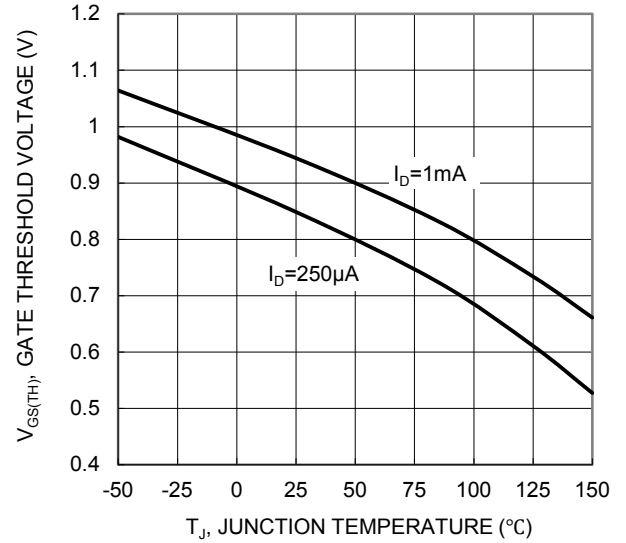


Figure 8. Gate Threshold Variation vs. Junction Temperature

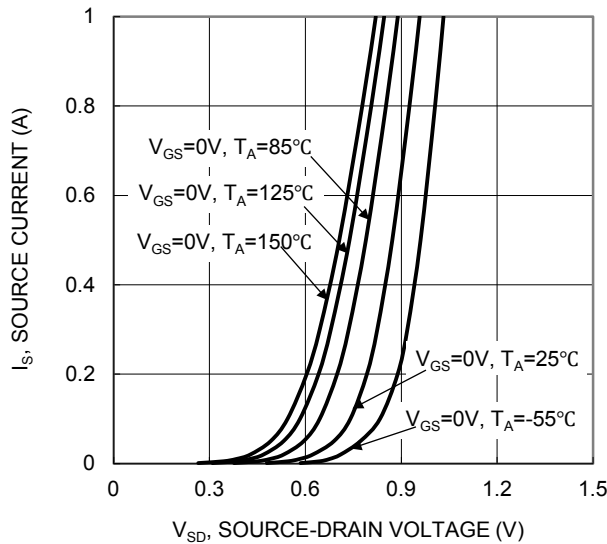


Figure 9. Diode Forward Voltage vs. Current

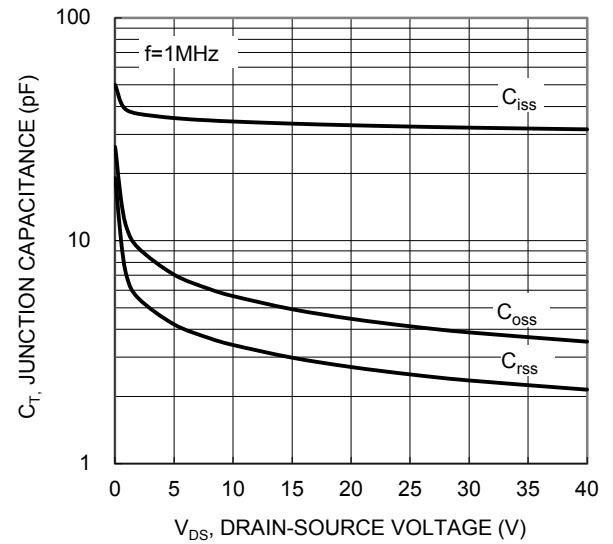


Figure 10. Typical Junction Capacitance

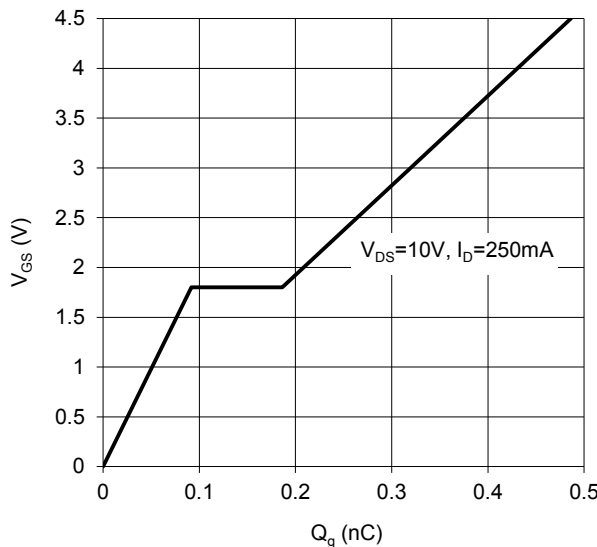


Figure 11. Gate Charge

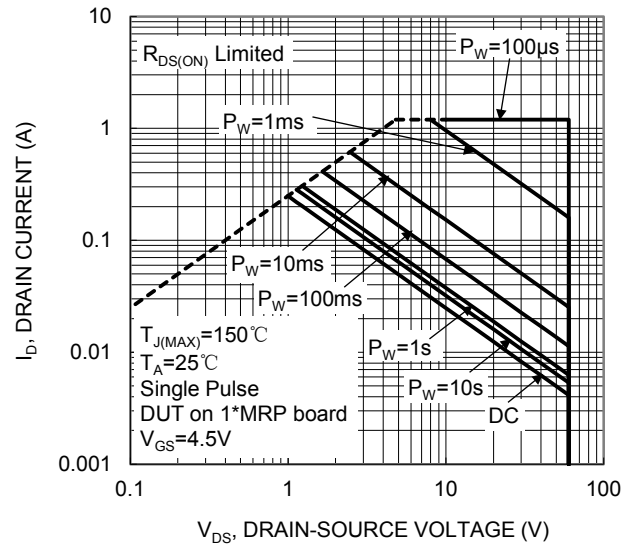


Figure 12. SOA, Safe Operation Area

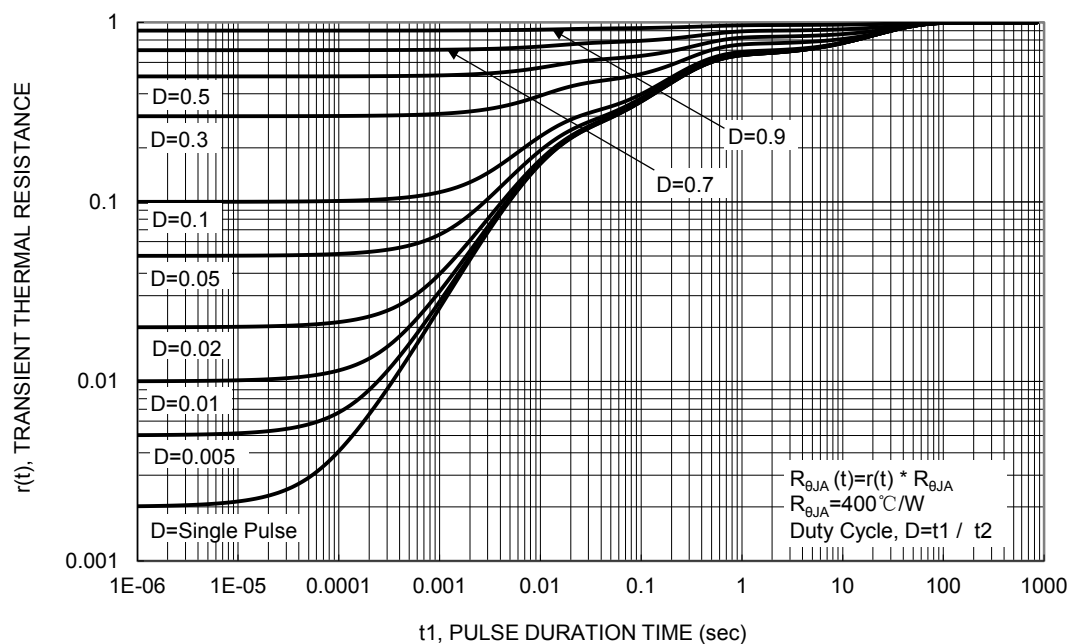
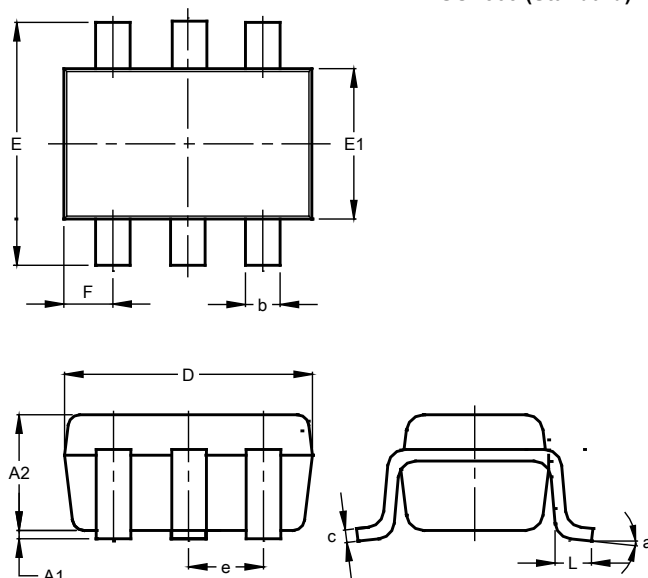


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

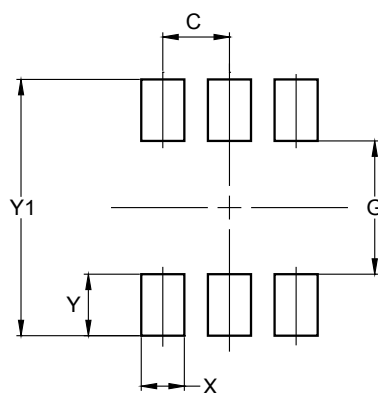


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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